INFORMATION DISCLOSURE CHATTON (Use several sheets if necessary)					Docket Number (Optional) YOR920030541U	Application Number 10/696,632			
					Applicant(s) Harold J. Hovel, et al.				
		(JAN 1 6 2004 8		Filing Date October 29, 2	Group Art Unit Unassigned			
U.S. PATENT DOCUMENTS									
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	U.S.		NAME	CLASS	SUBCLASS	FILING IP APPR	G DATE OPRIATE
TSB		6,429,145 Bl	8/6/02	Hove	:1				
				ļ	·······				
					<u> </u>				
		 	FOREIG	N PATE	INT DOCUMENTS	1	1	TRANSL	PTTON
	REF	DOCUMENT NUMBER	DATE		COUNTRY	CLASS	SUBCLASS	YES	NO
		•							
					·				
					uthor, Title, Date, Pertinen				
757		"Temperature And Magnetic Field Dependence Of The Carrier Mobility In SOI-Wafers By The Pseudo-MOSFET Method," Electrochemical Society Proceedings, by C. Rossel, et al., pp. 479-486							
TSP TSP		"Si Film Electrical Characterization in SOI Substrates by the HgFET Technique," Solid State Electronics, by H.J. Hovel pp. 1311-1333, 2003							
TSP TSP		"Extremely Low Resistivity Erbium Ohmic Contacts To n-type Silicon," Physics Letters, by P.L. Janega, et al., pp. 1415-1417							
TSP		"The Schottky-barrier Height Of The Contacts Between Some Rare-earth Metals (and silicides) And p-type Silicon," 1981 American Institute of Physics, by H. Norde, et al., pp. 865-867							
EXAMINER					Date considered 5/23/0 5				
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not									
considered. Include copy of this form with next communication to applicant.									